

UT2309

Power MOSFET

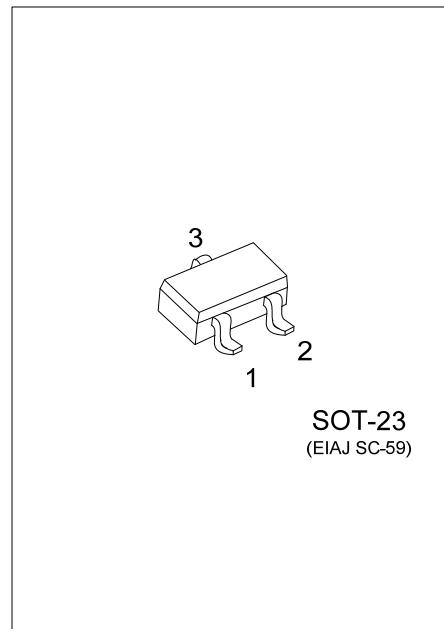
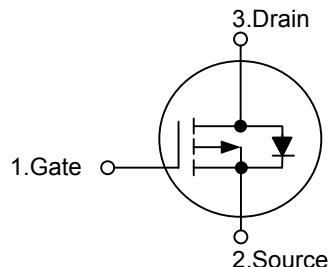
P-CHANNEL ENHANCEMENT
MODE

■ DESCRIPTION

The **UT2309** is P-channel power MOSFET, designed with high density cell with fast switching speed, ultra low on-resistance and excellent thermal and electrical capabilities.

Used in commercial and industrial surface mount applications and suited for low voltage applications such as DC/DC converters.

■ SYMBOL



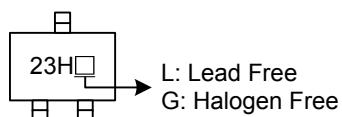
■ ORDERING INFORMATION

| Ordering Number | | Package | Pin Assignment | | | Packing |
|-----------------|---------------|---------|----------------|---|---|-----------|
| Lead Free | Halogen Free | | 1 | 2 | 3 | |
| UT2309L-AE3-R | UT2309G-AE3-R | SOT-23 | G | S | D | Tape Reel |

Note: Pin Assignment: G: Gate S: Source D: Drain

| | | |
|---------------|--|--|
| UT2309G-AE3-R | (1)Packing Type (2)Package Type (3)Green Package | (1) R: Tape Reel (2) AE3: SOT-23 (3) G: Halogen Free and Lead Free, L: Lead Free |
|---------------|--|--|

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS

| PARAMETER | SYMBOL | RATINGS | UNIT |
|-----------------------------------|-----------|------------|------|
| Drain-Source Voltage | V_{DSS} | -30 | V |
| Gate-Source Voltage | V_{GSS} | ± 20 | V |
| Continuous Drain Current (Note 3) | I_D | -3.7 | A |
| Pulsed Drain Current (Note 1, 2) | I_{DM} | -12 | A |
| Total Power Dissipation | P_D | 1.38 | W |
| Junction Temperature | T_J | +150 | °C |
| Storage Temperature | T_{STG} | -55 ~ +150 | °C |

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

| PARAMETER | SYMBOL | RATINGS | UNIT |
|------------------------------|---------------|---------|------|
| Junction to Ambient (Note 3) | θ_{JA} | 90 | °C/W |

■ ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise specified)

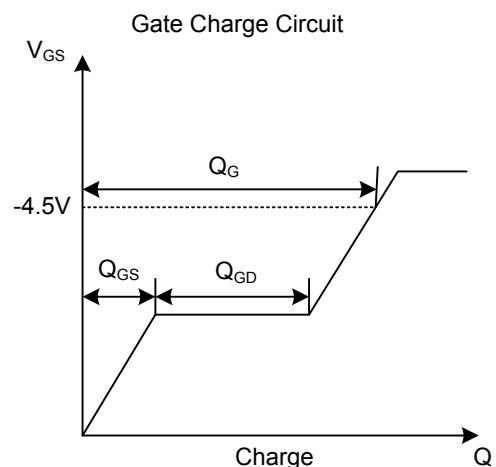
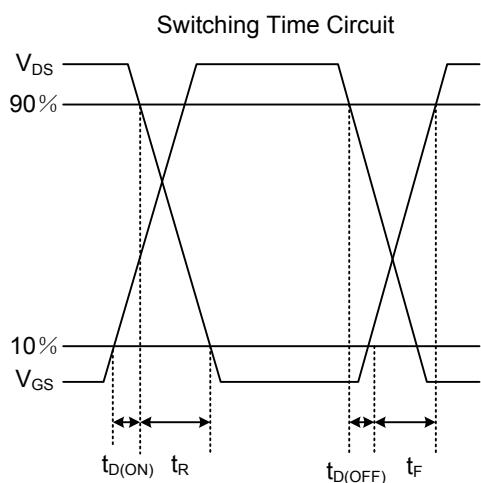
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--|---------------------|---|------|-----|------|------------------|
| OFF CHARACTERISTICS | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS}=0\text{ V}$, $I_D = -250\text{ }\mu\text{A}$ | -30 | | | V |
| Drain-Source Leakage Current | I_{DSS} | $V_{DS}=-30\text{V}$, $V_{GS}=0\text{V}$ | | | -0.5 | uA |
| Gate-Source Leakage Current | I_{GSS} | $V_{GS} = \pm 20\text{V}$, $V_{DS}=0\text{V}$ | | | 100 | nA |
| ON CHARACTERISTICS | | | | | | |
| Gate Threshold Voltage | $V_{GS(\text{TH})}$ | $V_{DS}=V_{GS}$, $I_D=-250\text{ }\mu\text{A}$ | -1.0 | | -3.0 | V |
| Static Drain-Source On-Resistance (Note 2) | $R_{DS(\text{ON})}$ | $V_{GS}=-10\text{V}$, $I_D=-3\text{A}$ | | | 75 | $\text{m}\Omega$ |
| | | $V_{GS}=-4.5\text{V}$, $I_D=-2.6\text{A}$ | | | 120 | $\text{m}\Omega$ |
| DYNAMIC CHARACTERISTICS | | | | | | |
| Input Capacitance | C_{ISS} | $V_{GS}=0\text{V}$, $V_{DS}=-25\text{V}$, $f=1.0\text{MHz}$ | | 626 | | pF |
| Output Capacitance | C_{OSS} | | | 95 | | pF |
| Reverse Transfer Capacitance | C_{RSS} | | | 81 | | pF |
| SWITCHING CHARACTERISTICS | | | | | | |
| Total Gate Charge (Note 2) | Q_G | $V_{DS}=-24\text{V}$, $V_{GS}=-4.5\text{V}$, $I_D=-3\text{A}$ | | 8.4 | | nC |
| Gate-Source Charge | Q_{GS} | | | 2.5 | | nC |
| Gate-Drain Charge | Q_{GD} | | | 3.6 | | nC |
| Turn-ON Delay Time (Note 2) | $t_{D(\text{ON})}$ | $V_{DS}=-15\text{V}$, $V_{GS}=-10\text{V}$, $I_D=-3\text{A}$, $R_G=3.3\Omega$ | | 6 | | ns |
| Turn-ON Rise Time | t_R | | | 15 | | ns |
| Turn-OFF Delay Time | $t_{D(\text{OFF})}$ | | | 19 | | ns |
| Turn-OFF Fall Time | t_F | | | 20 | | ns |
| SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS | | | | | | |
| Forward On Voltage | V_{SD} | $I_S=-1\text{A}$, $V_{GS}=0\text{V}$ | | | -1.2 | V |

Notes: 1. Repetitive rating, pulse width limited by junction temperature.

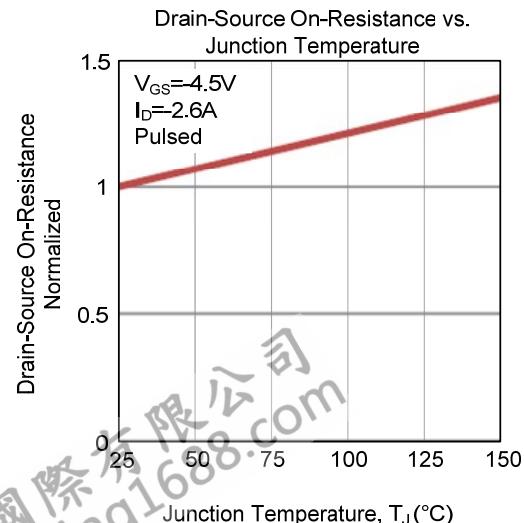
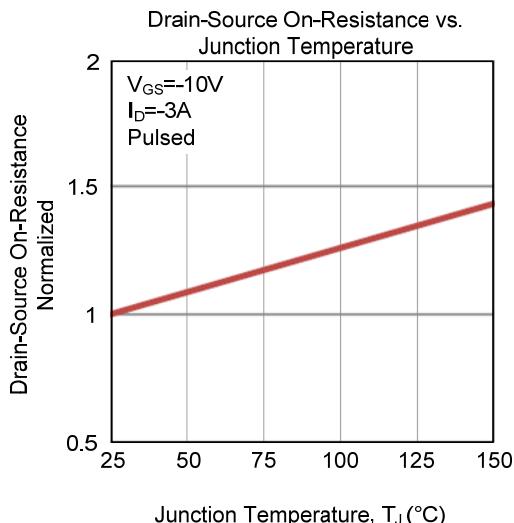
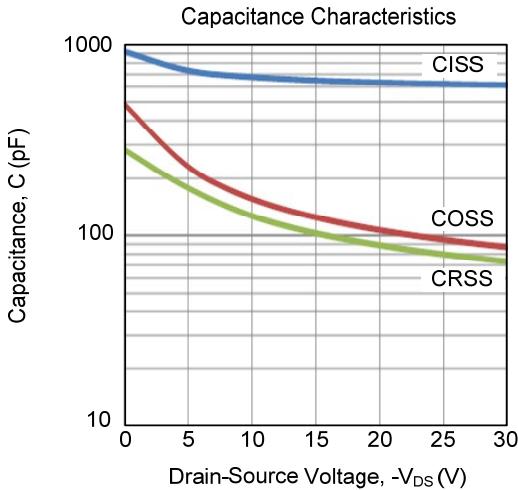
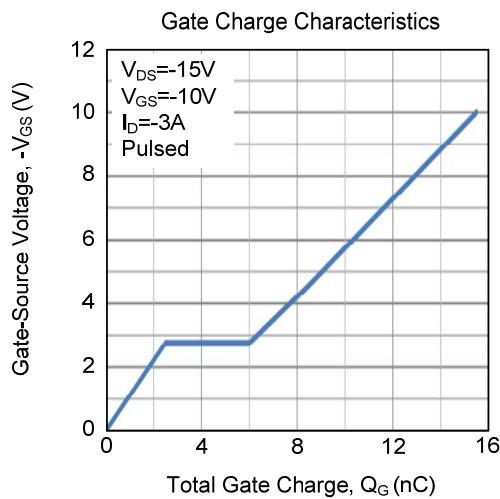
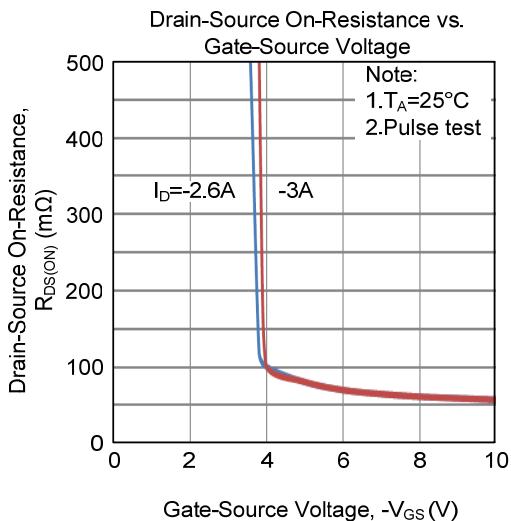
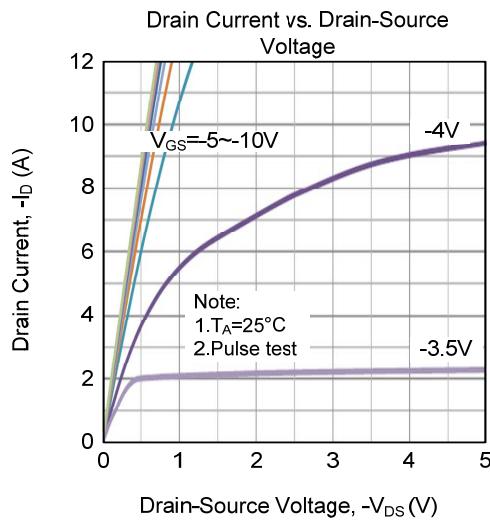
2. Pulse width $\leq 300\text{us}$, duty cycle $\leq 2\%$.

3. Surface mounted on 1 in ² copper pad of FR4 board.

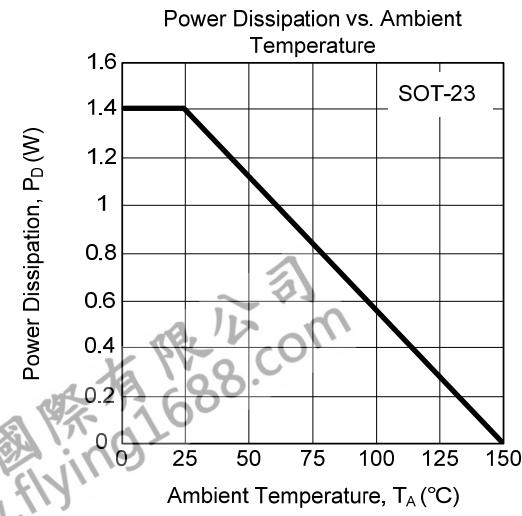
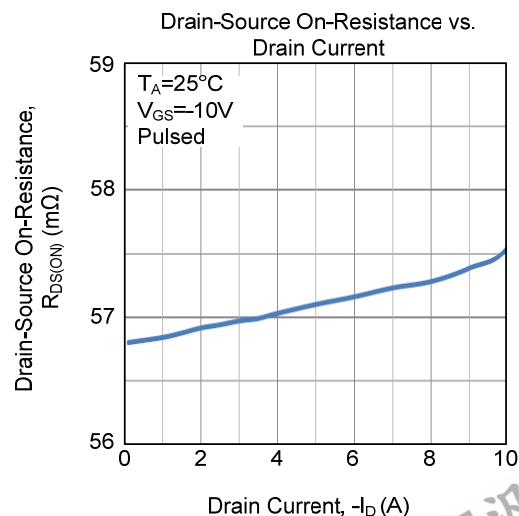
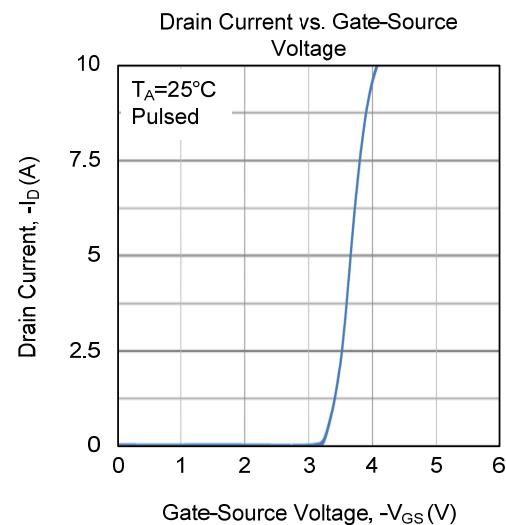
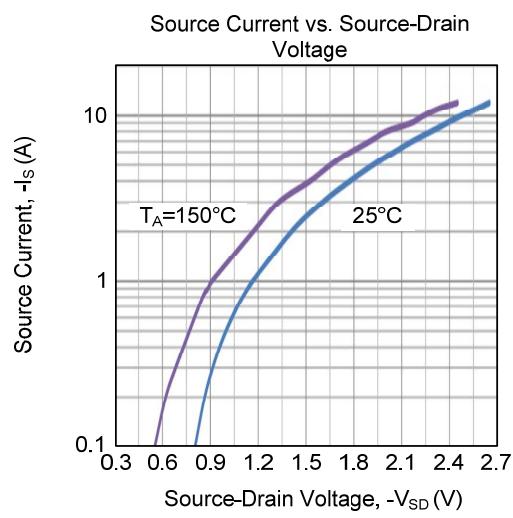
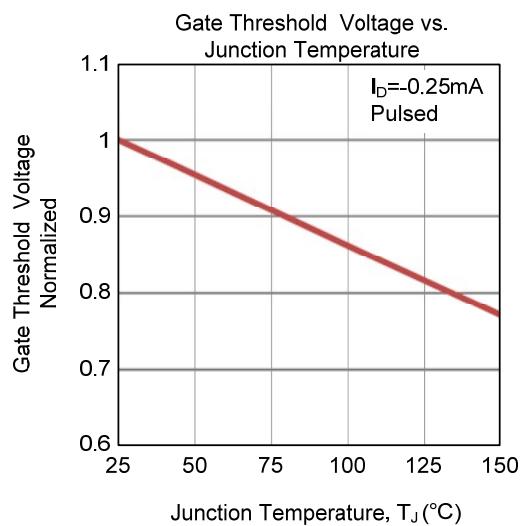
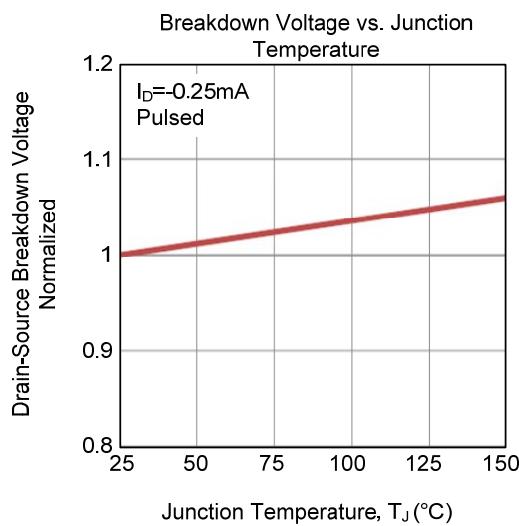
- TEST CIRCUITS AND WAVEFORMS



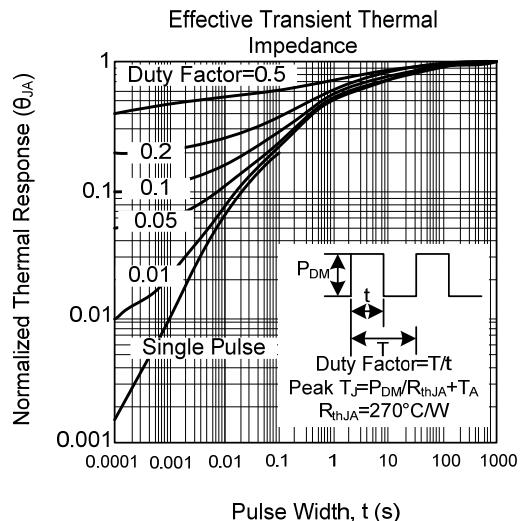
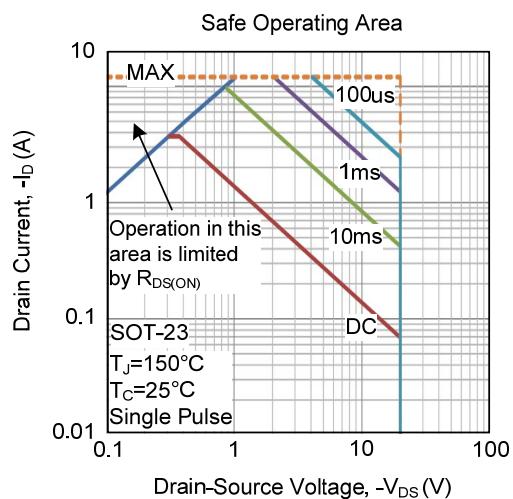
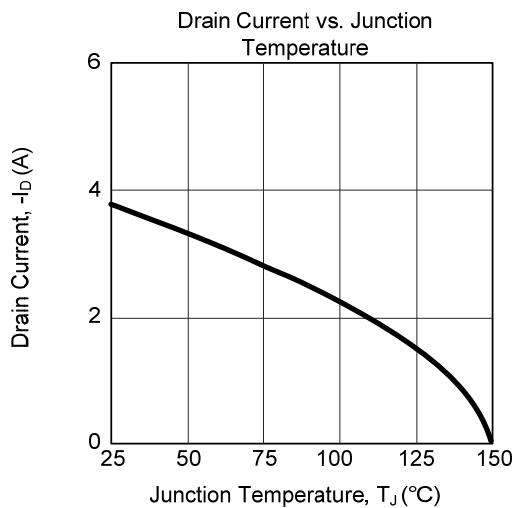
■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)



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